

Supplementary Material for:

## The pure spin current and fully spin-polarized current induced by photogalvanic effect and spin-Seebeck effect in halogen-decorated phosphorene

Zibin Zheng,<sup>a</sup> Lin Zhu,<sup>\*a</sup> Zenglin Cao,<sup>a</sup> Xiaohui Guo,<sup>a</sup> Yin Wang<sup>b</sup> and Kailun Yao<sup>a</sup>

<sup>a</sup> School of Physics and Wuhan National High Magnetic Field Center, Huazhong University of Science and Technology, Wuhan 430074, People's Republic of China

<sup>b</sup> International Centre for Quantum and Molecular Structures, Department of Physics, Shanghai University, Shanghai 200444, China

\* Author to whom correspondence should be addressed: [linzh@hust.edu.cn](mailto:linzh@hust.edu.cn)

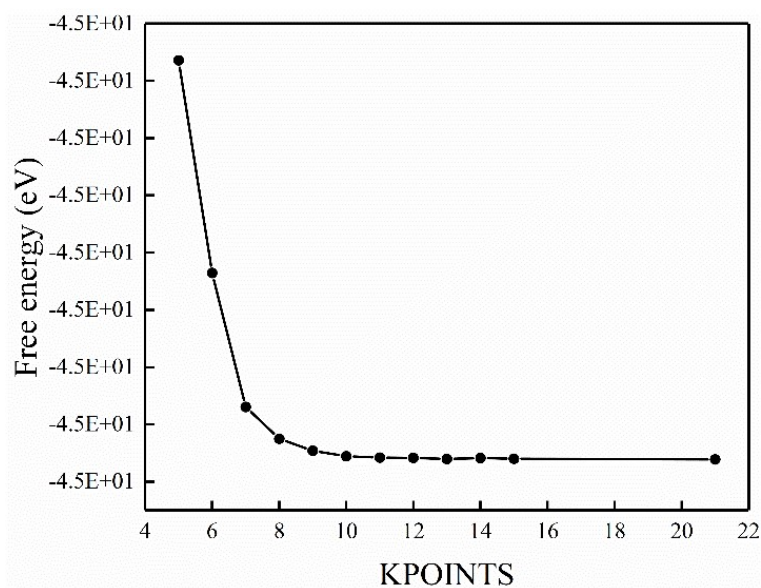
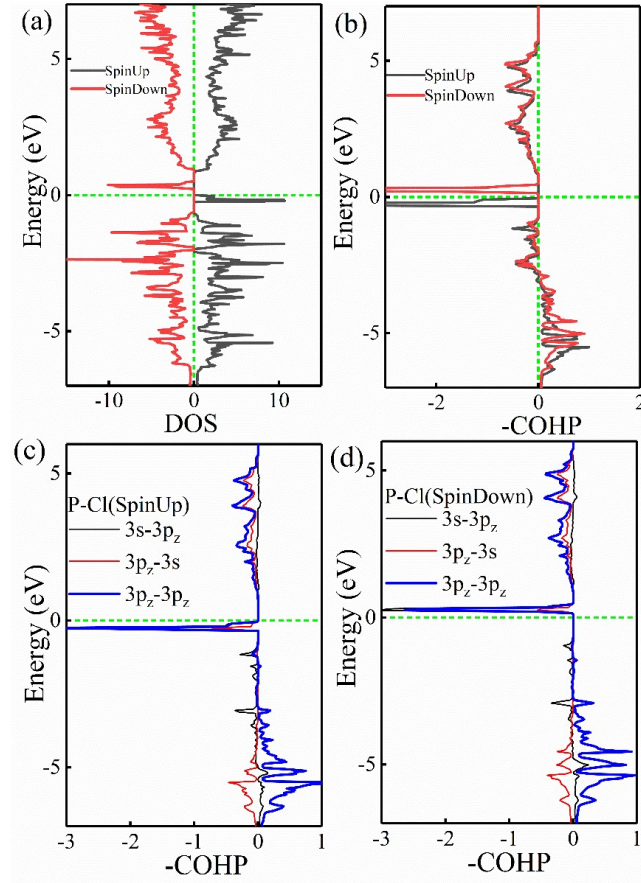
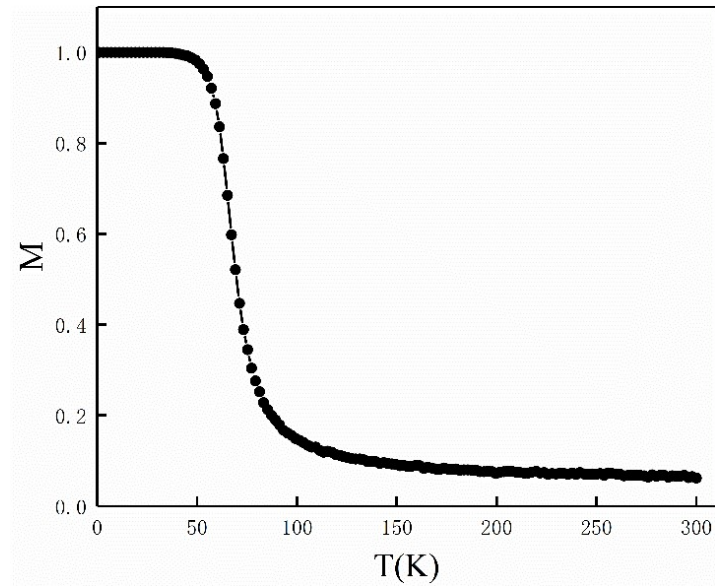


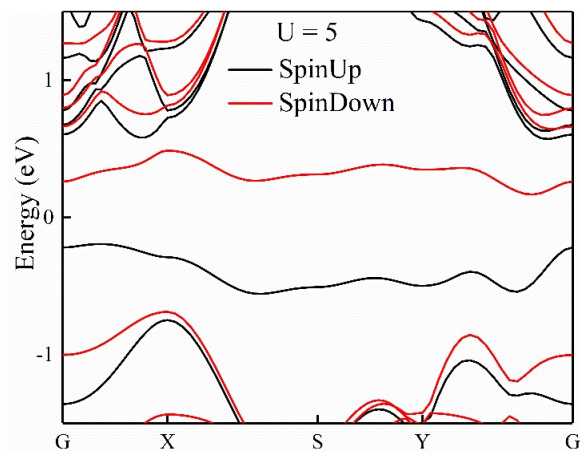
Fig. S1 The test of the number of k points.



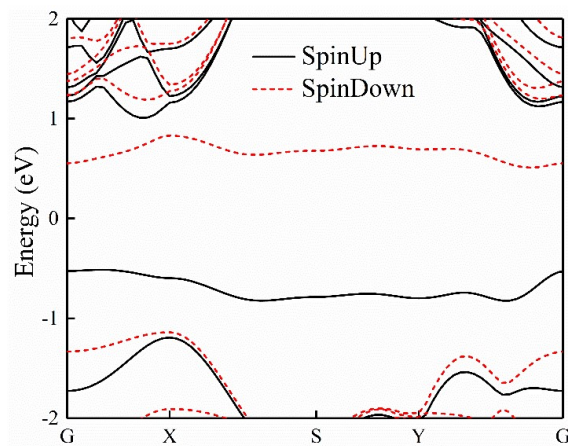
**Fig. S2** (a) The density of states (DOS). (b) The crystal orbital Hamilton population (COHP) analysis. (c) and (d) Single orbital COHPs analysis.



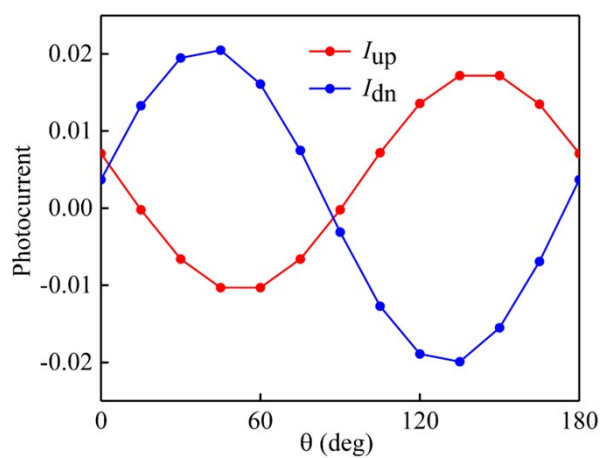
**Fig. S3** Variation of magnetic susceptibility with temperature.



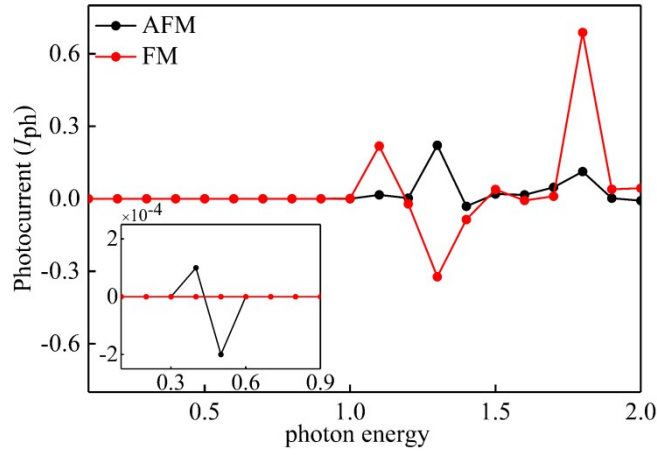
**Fig. S4** The band structures for  $U$  value of 5 ( $U$  for 3p electrons of P atoms and Cl atoms).



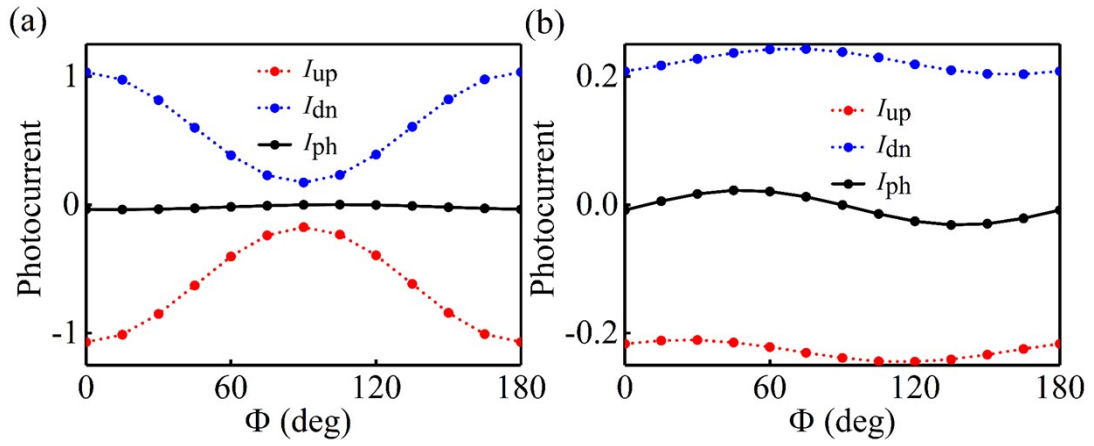
**Fig. S5** The band structures calculated by HSE06.



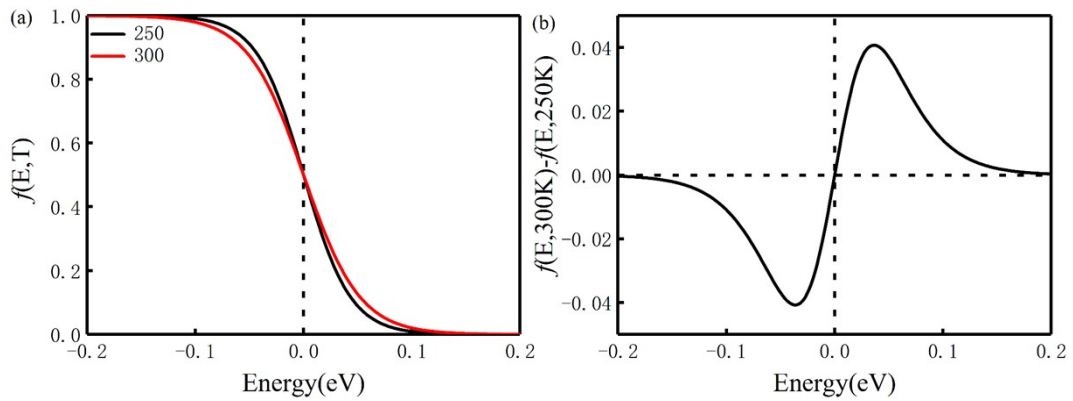
**Fig. S6** The photocurrent at the photon energy of 1.2 eV.



**Fig. S7**  $I_{ph}$  of FM and AFM at the the polarization angle  $\theta$  of  $45^\circ$ .

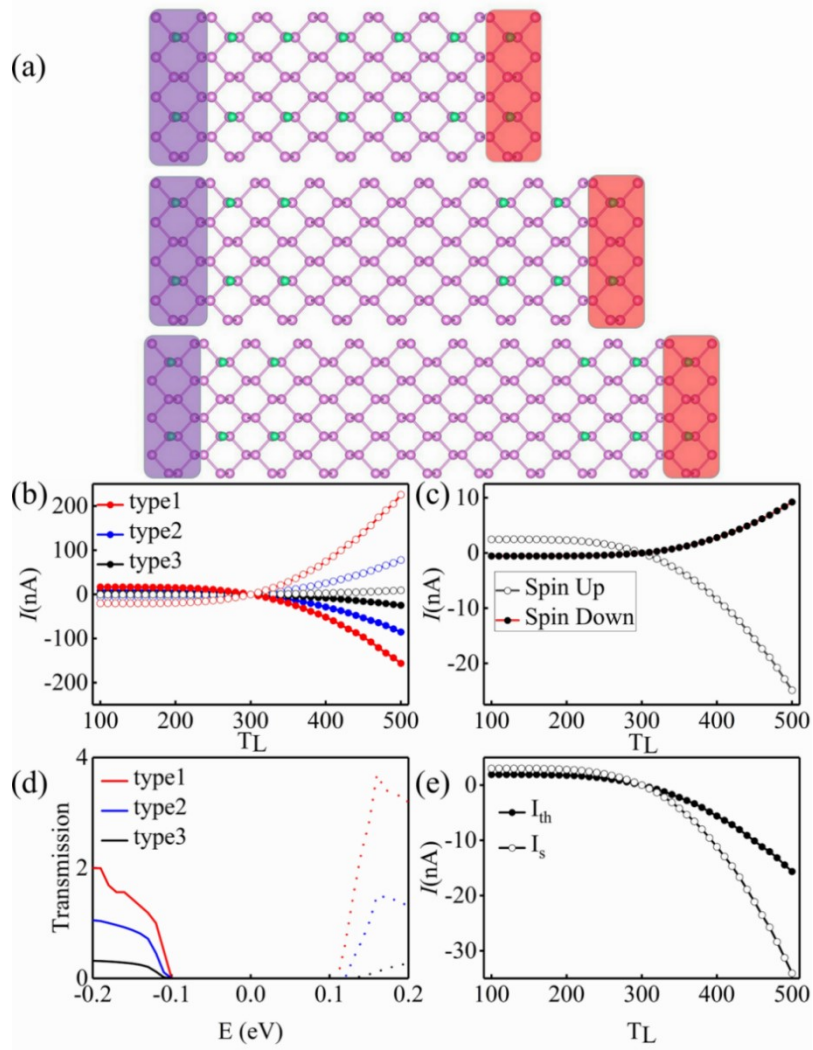


**Fig. S8** The photocurrent under CPL at the photon energy of 1.3 eV (a) and 1.8 eV (b).

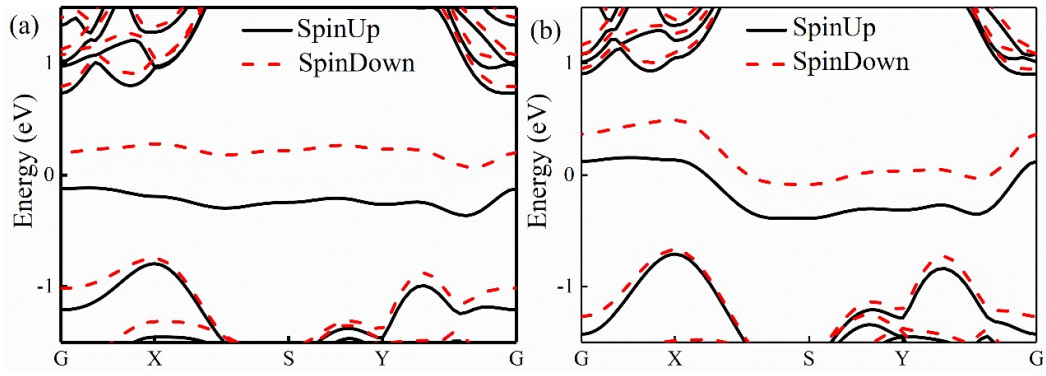


**Fig. S9** (a) Fermi-Dirac distribution function at the temperature of 250 K and 300 K.

(b) The Fermi distribution difference  $f_L(E, 300K) - f_R(E, 250K)$ .



**Fig. S10** (a) The device models of type1, type2 and type3. (b) The  $I_{\text{up}}$  and  $I_{\text{dn}}$  of the devices. (c) The  $I_{\text{up}}$  and  $I_{\text{dn}}$  of type3 device. Hollow and solid symbols represent spin up and spin down state respectively. (d) The transmission spectra of the devices. Solid lines and dotted lines represent spin up and spin down state, respectively. (e) The  $I_{\text{th}}$  and  $I_{\text{s}}$  of type3 device.



**Fig. S11** The band structures of (a) Br-decorated phosphorene and (b) F-decorated phosphorene.

**Table. S1** The bader charge analysis of system.

| Atom | X( Å) | Y( Å) | Z( Å)  | Charge(e) |
|------|-------|-------|--------|-----------|
| P1   | 2.479 | 2.715 | 7.821  | 0.04646   |
| P2   | 5.785 | 2.715 | 7.821  | -0.03830  |
| P3   | 2.479 | 1.899 | 9.932  | -0.28076  |
| P4   | 5.785 | 1.899 | 9.932  | -0.05247  |
| P5   | 0.826 | 0.401 | 9.932  | -0.05161  |
| P6   | 4.132 | 0.401 | 9.932  | -0.05161  |
| P7   | 0.826 | 4.206 | 7.821  | 0.00484   |
| P8   | 4.132 | 4.206 | 7.821  | 0.00484   |
| Cl   | 2.479 | 2.114 | 12.179 | 0.41861   |

**Table. S2** The band gap for different U values( U for the 3p electrons of P atoms and Cl atoms).

| U             | 1      | 2      | 3      | 4      | 5      |
|---------------|--------|--------|--------|--------|--------|
| Band Gap (eV) | 0.2612 | 0.2893 | 0.3157 | 0.3392 | 0.3610 |